Product	Type
Ultra Fast Rectifier Diodes	GPWH75610-4-02-3RD

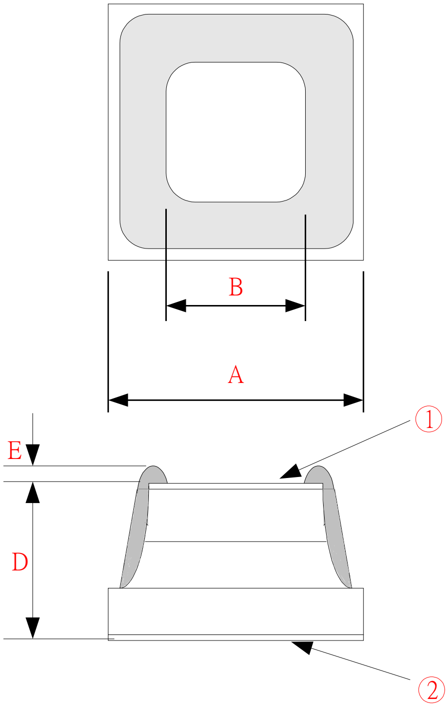
Metallization

Top Al ①

Bottom Ag ②

Dimension in mils

	Dimension
A	298±2
B	270(min.)
D	10.5±1
E	1.5.±1



Absolute Maximum Ratings (Ta=25℃)

PEAK REVERSE VOLTAGE VRM .. 1000 V

FORWARD

SURGE CURRENT IFSM….600 A

STORAGE TEMPERATURE RANGE Tstg .. –65~150℃

Electrical Characteristics

Item	Symbol	Test Condition	Standard
FORWARD VOLTAGE(for cell type)	VF	IF=70A	1.85 V (MAX)
REVERSE CURRENT	IR	VR=1000V	10μA (MAX)
REVERSE RECOVERY TIME	TRR	RG1	90ns
BREAKDOWN VOLTAGE	BVR	IR=10μA	1020V (MIN)

Quality Yield Assurance per wafer: 70%

Ho Chien Electronics Inc.	Spec No. GPWH75610-4-01	DATE：Sep.22.2006